

Abstract of the Disclosure

This invention provides a semiconductor device manufacturing method including forming a T type gate electrode having a wide region in an upper portion, the method including steps of: forming rectangular gate polysilicon; forming a nitride film covering the polysilicon; forming an oxide film thick on the nitride film; etching back the oxide film to expose the nitride film; etching the exposed nitride film, exposing the gate polysilicon, and forming a space; forming undoped polysilicon burying the space; etching back the undoped polysilicon to form a wide portion in the upper portion of the gate polysilicon; and etching the oxide film and the nitride film; siliciding the wide undoped silicon to form titanium silicide (or cobalt silicide). This manufacturing method makes it possible to easily form the T type gate electrode with good yield.